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Harrison  
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PATENT  
2658-0246P  
JUL 27 2001  
TECHNOLOGY CENTER 2800

Applicants: Keun No PARK

Conf: 9754

Serial No.: 09/725,572

Group: 2812

Filed: November 30, 2000

Examiner: A. Roman

For: METHOD OF PREVENTING GENERATION OF PARTICLES IN CHAMBER

RESPONSE UNDER 37 C.F.R. § 1.111

Honorable Commissioner for Patents  
Washington, D.C. 20231

July 26, 2001

Dear Sir:

Responsive to the non-final Office Action dated April 30, 2000, please enter the following remarks.

REMARKS

Claims 1-16 are pending in the present application. Claims 2 and 13 are independent.

Prior Art Rejections

Claims 1, 4 and 13-15 have been rejected under 35 U.S.C. § 102(e) as being anticipated by Seamons et al. (U.S. Patent No. 6,060,397). Applicant respectfully traverses this rejection.

Seamons et al. arguably teaches an in-situ method of cleaning residues from a chemical vapor deposition apparatus including introducing cleaning gases into a chamber to remove residues created by the use of the surface treatment gas (i.e. HMDS). As part of the method, Seamons et al. teaches introducing the cleaning gases (e.g. nitrogen) into the chamber after the last wafer has been removed and using the cleaning gases to remove residues in the chamber as volatile gases or plasma. See col. 2, lines 66-67 and col. 4, lines 30-36.